E. Lattice Semiconductor Corporation - <u>LFE3-95EA-6LFN1156I Datasheet</u>



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The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	490
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1156-BBGA
Supplier Device Package	1156-FPBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95ea-6lfn1156i

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LatticeECP3 Family Data Sheet Introduction

February 2012

Features

- Higher Logic Density for Increased System Integration
 - 17K to 149K LUTs
 - 116 to 586 I/Os
- Embedded SERDES
 - 150 Mbps to 3.2 Gbps for Generic 8b10b, 10-bit SERDES, and 8-bit SERDES modes
 - Data Rates 230 Mbps to 3.2 Gbps per channel for all other protocols
 - Up to 16 channels per device: PCI Express, SONET/SDH, Ethernet (1GbE, SGMII, XAUI), CPRI, SMPTE 3G and Serial RapidIO

■ sysDSP[™]

- Fully cascadable slice architecture
- 12 to 160 slices for high performance multiply and accumulate
- Powerful 54-bit ALU operations
- Time Division Multiplexing MAC Sharing
- Rounding and truncation
- Each slice supports
 - -Half 36x36, two 18x18 or four 9x9 multipliers
 - Advanced 18x36 MAC and 18x18 Multiply-
 - Multiply-Accumulate (MMAC) operations

■ Flexible Memory Resources

- Up to 6.85Mbits sysMEM[™] Embedded Block RAM (EBR)
- 36K to 303K bits distributed RAM
- sysCLOCK Analog PLLs and DLLs
 Two DLLs and up to ten PLLs per device
- Pre-Engineered Source Synchronous I/O
 - DDR registers in I/O cells

Table 1-1. LatticeECP3™ Family Selection Guide

• Dedicated read/write levelling functionality

Data Sheet DS1021

- Dedicated gearing logic
- Source synchronous standards support
 ADC/DAC, 7:1 LVDS, XGMII
 Link Speed ADC/DAC devices
 - -High Speed ADC/DAC devices
- Dedicated DDR/DDR2/DDR3 memory with DQS support
- Optional Inter-Symbol Interference (ISI) correction on outputs
- Programmable sysl/O[™] Buffer Supports Wide Range of Interfaces
 - On-chip termination
 - Optional equalization filter on inputs
 - LVTTL and LVCMOS 33/25/18/15/12
 - SSTL 33/25/18/15 I, II
 - HSTL15 I and HSTL18 I, II
 - PCI and Differential HSTL, SSTL
 - LVDS, Bus-LVDS, LVPECL, RSDS, MLVDS

Flexible Device Configuration

- Dedicated bank for configuration I/Os
- SPI boot flash interface
- Dual-boot images supported
- Slave SPI
- TransFR™ I/O for simple field updates
- Soft Error Detect embedded macro

System Level Support

- IEEE 1149.1 and IEEE 1532 compliant
- Reveal Logic Analyzer
- ORCAstra FPGA configuration utility
- · On-chip oscillator for initialization & general use
- 1.2 V core power supply

Device	ECP3-17	ECP3-35	ECP3-70	ECP3-95	ECP3-150
LUTs (K)	17	33	67	92	149
sysMEM Blocks (18 Kbits)	38	72	240	240	372
Embedded Memory (Kbits)	700	1327	4420	4420	6850
Distributed RAM Bits (Kbits)	36	68	145	188	303
18 x 18 Multipliers	24	64	128	128	320
SERDES (Quad)	1	1	3	3	4
PLLs/DLLs	2/2	4/2	10/2	10 / 2	10/2
Packages and SERDES Channels	/ I/O Combinatio	ns		•	
328 csBGA (10 x 10 mm)	2/116				
256 ftBGA (17 x 17 mm)	4 / 133	4 / 133			
484 fpBGA (23 x 23 mm)	4 / 222	4 / 295	4 / 295	4 / 295	
672 fpBGA (27 x 27 mm)		4 / 310	8 / 380	8 / 380	8 / 380
1156 fpBGA (35 x 35 mm)			12 / 490	12 / 490	16 / 586

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Primary Clock Routing

The purpose of the primary clock routing is to distribute primary clock sources to the destination quadrants of the device. A global primary clock is a primary clock that is distributed to all quadrants. The clock routing structure in LatticeECP3 devices consists of a network of eight primary clock lines (CLK0 through CLK7) per quadrant. The primary clocks of each quadrant are generated from muxes located in the center of the device. All the clock sources are connected to these muxes. Figure 2-12 shows the clock routing for one quadrant. Each quadrant mux is identical. If desired, any clock can be routed globally.

Figure 2-12. Per Quadrant Primary Clock Selection



Dynamic Clock Control (DCC)

The DCC (Quadrant Clock Enable/Disable) feature allows internal logic control of the quadrant primary clock network. When a clock network is disabled, all the logic fed by that clock does not toggle, reducing the overall power consumption of the device.

Dynamic Clock Select (DCS)

The DCS is a smart multiplexer function available in the primary clock routing. It switches between two independent input clock sources without any glitches or runt pulses. This is achieved regardless of when the select signal is toggled. There are two DCS blocks per quadrant; in total, there are eight DCS blocks per device. The inputs to the DCS block come from the center muxes. The output of the DCS is connected to primary clocks CLK6 and CLK7 (see Figure 2-12).

Figure 2-13 shows the timing waveforms of the default DCS operating mode. The DCS block can be programmed to other modes. For more information about the DCS, please see the list of technical documentation at the end of this data sheet.



Figure 2-13. DCS Waveforms



Secondary Clock/Control Sources

LatticeECP3 devices derive eight secondary clock sources (SC0 through SC7) from six dedicated clock input pads and the rest from routing. Figure 2-14 shows the secondary clock sources. All eight secondary clock sources are defined as inputs to a per-region mux SC0-SC7. SC0-SC3 are primary for control signals (CE and/or LSR), and SC4-SC7 are for the clock.

In an actual implementation, there is some overlap to maximize routability. In addition to SC0-SC3, SC7 is also an input to the control signals (LSR or CE). SC0-SC2 are also inputs to clocks along with SC4-SC7.





Note: Clock inputs can be configured in differential or single-ended mode.

Secondary Clock/Control Routing

Global secondary clock is a secondary clock that is distributed to all regions. The purpose of the secondary clock routing is to distribute the secondary clock sources to the secondary clock regions. Secondary clocks in the LatticeECP3 devices are region-based resources. Certain EBR rows and special vertical routing channels bind the secondary clock regions. This special vertical routing channel aligns with either the left edge of the center DSP slice in the DSP row or the center of the DSP row. Figure 2-15 shows this special vertical routing channel and the 20 secondary clock regions for the LatticeECP3 family of devices. All devices in the LatticeECP3 family have eight secondary clock resources per region (SC0 to SC7). The same secondary clock routing can be used for control signals.



MMAC DSP Element

The LatticeECP3 supports a MAC with two multipliers. This is called Multiply Multiply Accumulate or MMAC. In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value and with the result of the multiplier operation of operands BA and BB. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-28 shows the MMAC sysDSP element.



Figure 2-28. MMAC sysDSP Element



Programmable I/O Cells (PIC)

Each PIC contains two PIOs connected to their respective sysl/O buffers as shown in Figure 2-32. The PIO Block supplies the output data (DO) and the tri-state control signal (TO) to the sysl/O buffer and receives input from the buffer. Table 2-11 provides the PIO signal list.

Figure 2-32. PIC Diagram



* Signals are available on left/right/top edges only.

** Signals are available on the left and right sides only

*** Selected PIO.



Input signals are fed from the sysl/O buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In single data rate (SDR) the data is registered with the system clock by one of the registers in the single data rate sync register block.

In DDR mode, two registers are used to sample the data on the positive and negative edges of the modified DQS (ECLKDQSR) in the DDR Memory mode or ECLK signal when using DDR Generic mode, creating two data streams. Before entering the core, these two data streams are synchronized to the system clock to generate two data streams.

A gearbox function can be implemented in each of the input registers on the left and right sides. The gearbox function takes a double data rate signal applied to PIOA and converts it as four data streams, INA, IPA, INB and IPB. The two data streams from the first set of DDR registers are synchronized to the edge clock and then to the system clock before entering the core. Figure 2-30 provides further information on the use of the gearbox function.

The signal DDRCLKPOL controls the polarity of the clock used in the synchronization registers. It ensures adequate timing when data is transferred to the system clock domain from the ECLKDQSR (DDR Memory Interface mode) or ECLK (DDR Generic mode). The DDRLAT signal is used to ensure the data transfer from the synchronization registers to the clock transfer and gearbox registers.

The ECLKDQSR, DDRCLKPOL and DDRLAT signals are generated in the DQS Read Control Logic Block. See Figure 2-37 for an overview of the DQS read control logic.

Further discussion about using the DQS strobe in this module is discussed in the DDR Memory section of this data sheet.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.



Figure 2-38. LatticeECP3 Banks



LatticeECP3 devices contain two types of sysI/O buffer pairs.

1. Top (Bank 0 and Bank 1) and Bottom sysIO Buffer Pairs (Single-Ended Outputs Only)

The sysl/O buffer pairs in the top banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (both ratioed and referenced). One of the referenced input buffers can also be configured as a differential input. Only the top edge buffers have a programmable PCI clamp.

The two pads in the pair are described as "true" and "comp", where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

The top and bottom sides are ideal for general purpose I/O, PCI, and inputs for LVDS (LVDS outputs are only allowed on the left and right sides). The top side can be used for the DDR3 ADDR/CMD signals.

The I/O pins located on the top and bottom sides of the device (labeled PTxxA/B or PBxxA/B) are fully hot socketable. Note that the pads in Banks 3, 6 and 8 are wrapped around the corner of the device. In these banks, only the pads located on the top or bottom of the device are hot socketable. The top and bottom side pads can be identified by the Lattice Diamond tool.



Please see TN1177, LatticeECP3 sysIO Usage Guide for on-chip termination usage and value ranges.

Equalization Filter

Equalization filtering is available for single-ended inputs on both true and complementary I/Os, and for differential inputs on the true I/Os on the left, right, and top sides. Equalization is required to compensate for the difficulty of sampling alternating logic transitions with a relatively slow slew rate. It is considered the most useful for the Input DDRX2 modes, used in DDR3 memory, LVDS, or TRLVDS signaling. Equalization filter acts as a tunable filter with settings to determine the level of correction. In the LatticeECP3 devices, there are four settings available: 0 (none), 1, 2 and 3. The default setting is 0. The equalization logic resides in the sysI/O buffers, the two bits of setting is set uniquely in each input IOLOGIC block. Therefore, each sysI/O can have a unique equalization setting within a DQS-12 group.

Hot Socketing

LatticeECP3 devices have been carefully designed to ensure predictable behavior during power-up and powerdown. During power-up and power-down sequences, the I/Os remain in tri-state until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. Please refer to the Hot Socketing Specifications in the DC and Switching Characteristics in this data sheet.

SERDES and PCS (Physical Coding Sublayer)

LatticeECP3 devices feature up to 16 channels of embedded SERDES/PCS arranged in quads at the bottom of the devices supporting up to 3.2Gbps data rate. Figure 2-40 shows the position of the quad blocks for the LatticeECP3-150 devices. Table 2-14 shows the location of available SERDES Quads for all devices.

The LatticeECP3 SERDES/PCS supports a range of popular serial protocols, including:

- PCI Express 1.1
- Ethernet (XAUI, GbE 1000 Base CS/SX/LX and SGMII)
- Serial RapidIO
- SMPTE SDI (3G, HD, SD)
- CPRI
- SONET/SDH (STS-3, STS-12, STS-48)

Each quad contains four dedicated SERDES for high speed, full duplex serial data transfer. Each quad also has a PCS block that interfaces to the SERDES channels and contains protocol specific digital logic to support the standards listed above. The PCS block also contains interface logic to the FPGA fabric. All PCS logic for dedicated protocol support can also be bypassed to allow raw 8-bit or 10-bit interfaces to the FPGA fabric.

Even though the SERDES/PCS blocks are arranged in quads, multiple baud rates can be supported within a quad with the use of dedicated, per channel \div 1, \div 2 and \div 11 rate dividers. Additionally, multiple quads can be arranged together to form larger data pipes.

For information on how to use the SERDES/PCS blocks to support specific protocols, as well on how to combine multiple protocols and baud rates within a device, please refer to TN1176, LatticeECP3 SERDES/PCS Usage Guide.



LatticeECP3 Family Data Sheet DC and Switching Characteristics

April 2014

Data Sheet DS1021

Absolute Maximum Ratings^{1, 2, 3}

Supply Voltage V_CC
Supply Voltage V_{CCAUX} $\ldots \ldots \ldots \ldots -0.5$ V to 3.75 V
Supply Voltage V_{CCJ}
Output Supply Voltage V_{CCIO} –0.5 V to 3.75 V
Input or I/O Tristate Voltage Applied $^4.$ –0.5 V to 3.75 V
Storage Temperature (Ambient)
Junction Temperature (T_J) +125 °C

^{1.} Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

4. Overshoot and undershoot of -2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions¹

Symbol	Parameter	Min.	Max.	Units
V _{CC} ²	Core Supply Voltage	1.14	1.26	V
V _{CCAUX} ^{2, 4}	V _{CCAUX} ^{2,4} Auxiliary Supply Voltage, Terminating Resistor Switching Power Supply (SERDES)		3.465	V
V _{CCPLL}	PLL Supply Voltage	3.135	3.465	V
V _{CCIO} ^{2, 3}	I/O Driver Supply Voltage	1.14	3.465	V
V _{CCJ} ²	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
V_{REF1} and V_{REF2}	Input Reference Voltage	0.5	1.7	V
V _{TT} ⁵	Termination Voltage	0.5	1.3125	V
t _{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t _{JIND}	Junction Temperature, Industrial Operation	-40	100	°C
SERDES External Pow	er Supply ⁶			
V	Input Buffer Power Supply (1.2 V)	1.14	1.26	V
V CCIB	Input Buffer Power Supply (1.5 V)	1.425	1.575	V
V	Output Buffer Power Supply (1.2 V)		1.26	V
V CCOB	Output Buffer Power Supply (1.5 V)	1.425	1.575	V
V _{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	1.14	1.26	V

1. For correct operation, all supplies except V_{REF} and V_{TT} must be held in their valid operation range. This is true independent of feature usage.

If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as V_{CC.} If V_{CCIO} or V_{CCJ} is set to 3.3 V, they must be connected to the same power supply as V_{CCAUX}.

3. See recommended voltages by I/O standard in subsequent table.

4. V_{CCAUX} ramp rate must not exceed 30 mV/µs during power-up when transitioning between 0 V and 3.3 V.

5. If not used, V_{TT} should be left floating.

6. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for information on board considerations for SERDES power supplies.

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LVPECL33

The LatticeECP3 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL33



Table 3-3. LVPECL33 DC Conditions¹

Parameter	Description	Typical	Units
V _{CCIO}	Output Driver Supply (+/-5%)	3.30	V
Z _{OUT}	Driver Impedance	10	Ω
R _S	Driver Series Resistor (+/-1%)	93	Ω
R _P	Driver Parallel Resistor (+/-1%)	196	Ω
R _T	Receiver Termination (+/-1%)	100	Ω
V _{OH}	Output High Voltage	2.05	V
V _{OL}	Output Low Voltage	1.25	V
V _{OD}	Output Differential Voltage	0.80	V
V _{CM}	Output Common Mode Voltage	1.65	V
Z _{BACK}	Back Impedance	100.5	Ω
I _{DC}	DC Output Current	12.11	mA

Over Recommended Operating Conditions

1. For input buffer, see LVDS table.



RSDS25E

The LatticeECP3 devices support differential RSDS and RSDSE standards. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The RSDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-4 is one possible solution for RSDS standard implementation. Resistor values in Figure 3-4 are industry standard values for 1% resistors.



Figure 3-4. RSDS25E (Reduced Swing Differential Signaling)

Table 3-4. RSDS25E DC Conditions¹

Parameter	Description	Typical	Units
V _{CCIO}	Output Driver Supply (+/–5%)	2.50	V
Z _{OUT}	Driver Impedance	20	Ω
R _S	Driver Series Resistor (+/–1%)	294	Ω
R _P	Driver Parallel Resistor (+/-1%)	121	Ω
R _T	Receiver Termination (+/-1%)	100	Ω
V _{OH}	Output High Voltage	1.35	V
V _{OL}	Output Low Voltage	1.15	V
V _{OD}	Output Differential Voltage	0.20	V
V _{CM}	Output Common Mode Voltage	1.25	V
Z _{BACK}	Back Impedance	101.5	Ω
I _{DC}	DC Output Current	3.66	mA

Over Recommended Operating Conditions

1. For input buffer, see LVDS table.



LatticeECP3 External Switching Characteristics ^{1, 2, 3, 13}

			8		-8 -7		-6			
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units	
Clocks										
Primary Clock ⁶										
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-150EA	—	500	—	420	—	375	MHz	
t _{w_PRI}	Clock Pulse Width for Primary Clock	ECP3-150EA	0.8	—	0.9	—	1.0		ns	
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-150EA	—	300	_	330	—	360	ps	
t _{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-150EA	—	250		280	—	300	ps	
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-70EA/95EA	—	500	_	420	—	375	MHz	
tw_pri	Pulse Width for Primary Clock	ECP3-70EA/95EA	0.8	—	0.9	—	1.0	—	ns	
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-70EA/95EA	_	360	_	370	_	380	ps	
t _{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-70EA/95EA	—	310	_	320	—	330	ps	
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-35EA	—	500	—	420	—	375	MHz	
tw_pri	Pulse Width for Primary Clock	ECP3-35EA	0.8	—	0.9	—	1.0	—	ns	
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-35EA	_	300	_	330	—	360	ps	
t _{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-35EA	—	250	_	280	—	300	ps	
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-17EA	—	500	_	420	—	375	MHz	
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-17EA	0.8	—	0.9	—	1.0	_	ns	
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-17EA	_	310	_	340	—	370	ps	
t _{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-17EA	—	220	_	230	—	240	ps	
Edge Clock ⁶										
fMAX_EDGE	Frequency for Edge Clock	ECP3-150EA	—	500	—	420		375	MHz	
tw_edge	Clock Pulse Width for Edge Clock	ECP3-150EA	0.9	—	1.0	—	1.2	_	ns	
tskew_edge_dqs	Edge Clock Skew Within an Edge of the Device	ECP3-150EA	_	200	_	210	—	220	ps	
fMAX_EDGE	Frequency for Edge Clock	ECP3-70EA/95EA	—	500	_	420	—	375	MHz	
tw_edge	Clock Pulse Width for Edge Clock	ECP3-70EA/95EA	0.9	—	1.0	—	1.2	—	ns	
tskew_edge_dqs	Edge Clock Skew Within an Edge of the Device	ECP3-70EA/95EA	_	200	_	210	—	220	ps	
fMAX_EDGE	Frequency for Edge Clock	ECP3-35EA	—	500	—	420	—	375	MHz	
tw_edge	Clock Pulse Width for Edge Clock	ECP3-35EA	0.9	—	1.0	—	1.2	_	ns	
tskew_edge_dqs	Edge Clock Skew Within an Edge of the Device	ECP3-35EA	_	200	_	210	—	220	ps	
f _{MAX_EDGE}	Frequency for Edge Clock	ECP3-17EA	—	500	_	420	—	375	MHz	
tw_edge	Clock Pulse Width for Edge Clock	ECP3-17EA	0.9	—	1.0	—	1.2	_	ns	
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-17EA	—	200	_	210	—	220	ps	
Generic SDR										
General I/O Pin Par	ameters Using Dedicated Clock In	put Primary Clock W	Vithout Pl	LL ²						
t _{co}	Clock to Output - PIO Output Register	ECP3-150EA		3.9		4.3	_	4.7	ns	
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.0	_	0.0		0.0	_	ns	
t _H	Clock to Data Hold - PIO Input Register	ECP3-150EA	1.5	_	1.7	_	2.0		ns	
	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.3	_	1.5	_	1.7	—	ns	



LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

			-	-8	-	-7	-	-6	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	0.0	-	0.0	—	0.0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-150EA	_	500	_	420	_	375	MHz
t _{CO}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.8	—	4.2	—	4.6	ns
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	_	ns
t _H	Clock to Data Hold - PIO Input Register	ECP3-70EA/95EA	1.4	—	1.6	_	1.8	_	ns
	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70EA/95EA	1.3	—	1.5	_	1.7	_	ns
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t _{CO}	Clock to Output - PIO Output Register	ECP3-35EA	—	3.7	—	4.1	—	4.5	ns
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
t _H	Clock to Data Hold - PIO Input Register	ECP3-35EA	1.2	—	1.4	—	1.6	—	ns
t _{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-35EA	1.3	—	1.4	—	1.5	—	ns
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-35EA	0.0	_	0.0	—	0.0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-35EA	—	500	—	420	—	375	MHz
t _{co}	Clock to Output - PIO Output Register	ECP3-17EA	—	3.5	—	3.9	—	4.3	ns
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
t _H	Clock to Data Hold - PIO Input Register	ECP3-17EA	1.3	—	1.5	—	1.6	—	ns
t _{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-17EA	1.3	—	1.4	—	1.5	—	ns
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-17EA	—	500	_	420	—	375	MHz
General I/O Pin Par	rameters Using Dedicated Clock I	nput Primary Clock w	ith PLL v	vith Cloc	k Injectio	on Remo	val Settir	ng²	-
t _{COPLL}	Clock to Output - PIO Output Register	ECP3-150EA	—	3.3	—	3.6	—	39	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.7	—	0.8	—	0.9	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
tSU_DELPLL	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.6	—	1.8	—	2.0	—	ns
^t H_DELPLL	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	—	0.0	—	0.0	—	0.0	ns
t _{COPLL}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.3	—	3.5	—	3.8	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.7		0.8		0.9		ns



LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

			-8		-8 -7		-6		
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{DVECLKGDDR}	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDRX1 Clock Frequency	All ECP3EA Devices	_	250	_	250	_	250	MHz
Generic DDRX2 Inputs with Clock and Data (>10 Bits Wide) Centered at Pin (GDDRX2_RX.ECLK.Centered) Using PCLK Pin for Clock Input									
Left and Right Sid	les								
t _{SUGDDR}	Data Setup Before CLK	ECP3-150EA	321		403		471		ps
t _{HOGDDR}	Data Hold After CLK	ECP3-150EA	321	_	403	—	471	—	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA		405	_	325	_	280	MHz
t _{SUGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	321		403		535		ps
t _{HOGDDR}	Data Hold After CLK	ECP3-70EA/95EA	321	_	403		535	—	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA		405	_	325	_	250	MHz
t _{SUGDDR}	Data Setup Before CLK	ECP3-35EA	335		425		535	—	ps
t _{HOGDDR}	Data Hold After CLK	ECP3-35EA	335		425		535	—	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	_	405	_	325		250	MHz
t _{SUGDDR}	Data Setup Before CLK	ECP3-17EA	335		425		535		ps
t _{HOGDDR}	Data Hold After CLK	ECP3-17EA	335		425		535		ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	_	405		325		250	MHz
Generic DDRX2 In	puts with Clock and Data (>10	Bits Wide) Aligned at Pin	(GDDR)	(2_RX.EC	CLK.Alig	ned)	•		
Left and Right Sid	le Using DLLCLKIN Pin for Cloo	ck Input							
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225		0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775		0.775	_	0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	_	460	_	385		345	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-70EA/95EA	_	0.225	—	0.225		0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775	_	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	_	460	—	385	_	311	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-35EA	_	0.210	_	0.210	_	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790	_	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	_	460	—	385	_	311	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-17EA	—	0.210	_	0.210	_	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790	_	0.790	—	0.790	_	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA		460		385	_	311	MHz
Top Side Using P	CLK Pin for Clock Input								
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-150EA		0.225	_	0.225		0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-150EA	0.775		0.775	_	0.775	_	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA		235		170	—	130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-70EA/95EA		0.225		0.225		0.225	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-70EA/95EA	0.775	_	0.775	—	0.775	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA		235		170	_	130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-35EA		0.210	_	0.210	—	0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-35EA	0.790	_	0.790	—	0.790	—	UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA		235		170		130	MHz
t _{DVACLKGDDR}	Data Setup Before CLK	ECP3-17EA		0.210		0.210		0.210	UI
t _{DVECLKGDDR}	Data Hold After CLK	ECP3-17EA	0.790		0.790		0.790		UI
f _{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	—	235	—	170	—	130	MHz



LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

			· 	-8	_	7	_	6	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
fMAX GDDB	DDRX1 Clock Frequency	ECP3-70EA/95EA		250		250	_	250	MHz
	Data Valid Before CLK	ECP3-35EA	683	—	688	_	690	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-35EA	683	_	688	_	690	_	ps
f _{MAX GDDR}	DDRX1 Clock Frequency	ECP3-35EA	_	250	_	250	_	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-17EA	683	—	688	_	690	_	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-17EA	683	—	688	—	690	—	ps
f _{MAX} GDDR	DDRX1 Clock Frequency	ECP3-17EA	_	250	_	250	—	250	MHz
Generic DDRX1 Ou	itput with Clock and Data Aligned	at Pin (GDDRX1_TX.	SCLK.Ali	gned) ¹⁰					
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-150EA	—	335	—	338	—	341	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-150EA		335	_	338	—	341	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA		250	_	250	—	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-70EA/95EA	_	339	_	343	—	347	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-70EA/95EA	_	339	_	343	—	347	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	_	250	_	250	—	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-35EA	_	322	_	320	—	321	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-35EA	_	322	_	320	—	321	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	_	250	_	250	—	250	MHz
t _{DIBGDDR}	Data Invalid Before Clock	ECP3-17EA	_	322	_	320	—	321	ps
t _{DIAGDDR}	Data Invalid After Clock	ECP3-17EA	_	322	_	320	—	321	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA		250	_	250	—	250	MHz
Generic DDRX1 Ou	itput with Clock and Data (<10 Bi	ts Wide) Centered at P	in (GDD	RX1_TX.	DQS.Cen	tered) ¹⁰			
Left and Right Side	es								
t _{DVBGDDR}	Data Valid Before CLK	ECP3-150EA	670	_	670	—	670	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	_	250		250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-70EA/95EA	657	—	652	_	650	_	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	_	250	_	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-35EA	670	—	675	—	676	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-35EA	670	—	675	_	676	_	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	_	250	_	250	—	250	MHz
t _{DVBGDDR}	Data Valid Before CLK	ECP3-17EA	670	—	670	—	670	—	ps
t _{DVAGDDR}	Data Valid After CLK	ECP3-17EA	670	—	670	—	670	—	ps
f _{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	_	250	_	250	—	250	MHz
Generic DDRX2 Ou	itput with Clock and Data (>10 Bi	ts Wide) Aligned at Pir	n (GDDR	X2_TX.A	igned)				
Left and Right Side	25								
t _{DIBGDDR}	Data Invalid Before Clock	All ECP3EA Devices		200		210		220	ps
t _{DIAGDDR}	Data Invalid After Clock	All ECP3EA Devices	_	200	_	210	_	220	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	_	500	_	420	—	375	MHz
Generic DDRX2 Ou	Itput with Clock and Data (>10 Bi	ts Wide) Centered at P	in Using		L (GDDF	X2_TX.D	QSDLL.	Centered)11
Left and Right Side	es								
t _{DVBGDDR}	Data Valid Before CLK	All ECP3EA Devices	400		400		431		ps
t _{DVAGDDR}	Data Valid After CLK	All ECP3EA Devices	400		400	—	432		ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	_	400	_	400	—	375	MHz







Figure 3-7. DDR/DDR2/DDR3 Parameters





Figure 3-8. Generic DDRX1/DDRX2 (With Clock Center on Data Window)





SERDES External Reference Clock

The external reference clock selection and its interface are a critical part of system applications for this product. Table 3-12 specifies reference clock requirements, over the full range of operating conditions.

Symbol	Description	Min.	Тур.	Max.	Units
F _{REF}	Frequency range	15	_	320	MHz
F _{REF-PPM}	Frequency tolerance ¹	-1000	_	1000	ppm
V _{REF-IN-SE}	Input swing, single-ended clock ²	200	_	V _{CCA}	mV, p-p
V _{REF-IN-DIFF}	Input swing, differential clock	200	_	2*V _{CCA}	mV, p-p differential
V _{REF-IN}	Input levels	0	_	V _{CCA} + 0.3	V
D _{REF}	Duty cycle ³	40	_	60	%
T _{REF-R}	Rise time (20% to 80%)	200	500	1000	ps
T _{REF-F}	Fall time (80% to 20%)	200	500	1000	ps
Z _{REF-IN-TERM-DIFF}	Differential input termination	-20%	100/2K	+20%	Ohms
C _{REF-IN-CAP}	Input capacitance	_	—	7	pF

Table 3-12. External Reference Clock Specification (refclkp/refclkn)

1. Depending on the application, the PLL_LOL_SET and CDR_LOL_SET control registers may be adjusted for other tolerance values as described in TN1176, LatticeECP3 SERDES/PCS Usage Guide.

2. The signal swing for a single-ended input clock must be as large as the p-p differential swing of a differential input clock to get the same gain at the input receiver. Lower swings for the clock may be possible, but will tend to increase jitter.

3. Measured at 50% amplitude.

Figure 3-13. SERDES External Reference Clock Waveforms





Switching Test Conditions

Figure 3-33 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-23.

Figure 3-33. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

Table 3-23. Te	est Fixture Required	Components,	Non-Terminated Interfaces
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Test Condition	R ₁	R ₂	CL	Timing Ref.	V _T
LVTTL and other LVCMOS settings (L -> H, H -> L)	8	8	0 pF	LVCMOS 3.3 = 1.5V	
				LVCMOS 2.5 = $V_{CCIO}/2$	
				LVCMOS 1.8 = V _{CCIO} /2	
				LVCMOS 1.5 = $V_{CCIO}/2$	_
				LVCMOS 1.2 = V _{CCIO} /2	_
LVCMOS 2.5 I/O (Z -> H)	x	1MΩ	0 pF	V _{CCIO} /2	
LVCMOS 2.5 I/O (Z -> L)	1 MΩ	x	0 pF	V _{CCIO} /2	V _{CCIO}
LVCMOS 2.5 I/O (H -> Z)	8	100	0 pF	V _{OH} - 0.10	
LVCMOS 2.5 I/O (L -> Z)	100	x	0 pF	V _{OL} + 0.10	V _{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.



Signal Descriptions (Cont.)

Signal Name	I/O	Description		
D7/SPID0	I/O	Parallel configuration I/O. SPI/SPIm data input. Open drain during configura- tion.		
DI/CSSPI0N/CEN	I/O	Serial data input for slave serial mode. SPI/SPIm mode chip select.		
Dedicated SERDES Signals ³				
PCS[Index]_HDINNm	I	High-speed input, negative channel m		
PCS[Index]_HDOUTNm	0	High-speed output, negative channel m		
PCS[Index]_REFCLKN	I	Negative Reference Clock Input		
PCS[Index]_HDINPm	I	High-speed input, positive channel m		
PCS[Index]_HDOUTPm	0	High-speed output, positive channel m		
PCS[Index]_REFCLKP	I	Positive Reference Clock Input		
PCS[Index]_VCCOBm		Output buffer power supply, channel m (1.2V/1.5)		
PCS[Index]_VCCIBm		Input buffer power supply, channel m (1.2V/1.5V)		

1. When placing switching I/Os around these critical pins that are designed to supply the device with the proper reference or supply voltage, care must be given.

2. These pins are dedicated inputs or can be used as general purpose I/O.

3. m defines the associated channel in the quad.